

CSD83325L 12V 双路 N 通道 NexFET™ 功率 MOSFET

1 特性

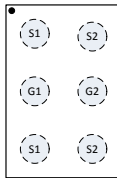
- 共漏极配置
- 低导通电阻
- 2.2mm x 1.15mm 的小尺寸
- 无铅
- 符合 RoHS
- 无卤素
- 栅极 ESD 保护

2 应用

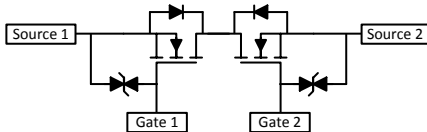
- 电池管理
- 电池保护

3 说明

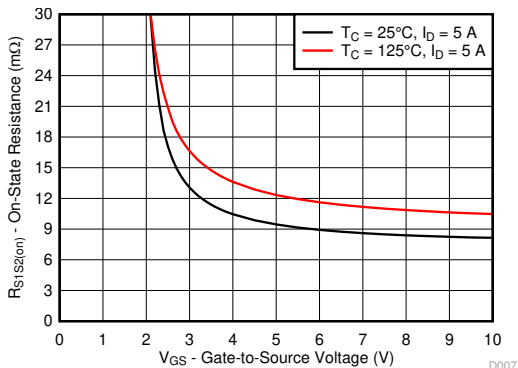
这款 12V、9.9mΩ、2.2mm x 1.15mm LGA 双路 NexFET™ 功率 MOSFET 旨在以小巧封装更大程度地降低电阻和栅极电荷。该器件尺寸小巧并采用共漏极配置，非常适合小型手持设备的电池包应用。



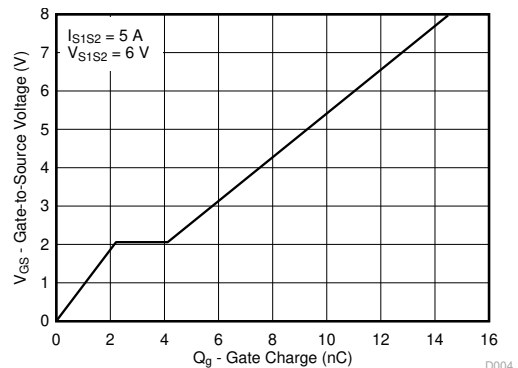
顶视图



配置



$R_{DS(on)}$ 与 V_{GS} 之间的关系



栅极电荷

产品概要

$T_A = 25^\circ\text{C}$		典型值	单位
V_{S1S2}	源电压	12	V
Q_g	栅极电荷总量 (4.5V)	8.4	nC
Q_{gd}	栅极电荷 (栅极到漏极)	1.9	nC
$R_{S1S2(on)}$	源极至源极导通电阻	$V_{GS} = 2.5\text{V}$	17.5 mΩ
		$V_{GS} = 3.8\text{V}$	10.9 mΩ
		$V_{GS} = 4.5\text{V}$	9.9 mΩ
$V_{GS(th)}$	阈值电压	1.0	V

器件信息(1)

器件	数量	介质	封装	出货
CSD83325L	3000	7 英寸卷带	2.20mm x 1.15mm Land Grid Array (LGA) 封装	卷带包装
CSD83325LT	250			

- (1) 如需了解所有可用封装，请参阅数据表末尾的可订购产品附录。

绝对最大额定值

$T_A = 25^\circ\text{C}$		值	单位
V_{S1S2}	源电压	12	V
V_{GS}	栅源电压	± 10	V
I_S	持续源极电流 ⁽¹⁾	8	A
I_{SM}	脉冲源极电流 ⁽²⁾	52	A
P_D	功率耗散	2.3	W
$V_{(ESD)}$	人体放电模型 (HBM)	2000	V
T_J 、 T_{stg}	工作结温， 贮存温度	-55 至 150	$^\circ\text{C}$

- (1) 器件在 105°C 温度下运行。
(2) $R_{\theta JA} = 150^\circ\text{C/W}$ (覆铜面积最小时的典型值)，脉冲持续时间 $\leq 100\mu\text{s}$ ，占空比 $\leq 1\%$ 。



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4 Specifications

4.1 Electrical Characteristics

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV _{S1S2}	Source-to-source voltage	V _{GS} = 0 V, I _S = 250 μA	12			V
I _{S1S2}	Source-to-source leakage current	V _{GS} = 0 V, V _{S1S2} = 9.6 V	1.0			μA
I _{GSS}	Gate-to-source leakage current	V _{S1S2} = 0 V, V _{GS} = 10 V	10			μA
V _{GS(th)}	Gate-to-source threshold voltage	V _{S1S2} = V _{GS} , I _S = 250 μA	0.7	1.0	1.4	V
R _{S1S2(on)}	Source-to-source on resistance	V _{GS} = 2.5 V, I _S = 5 A	12.0	17.5	23.0	mΩ
		V _{GS} = 3.8 V, I _S = 5 A	8.8	10.9	13.0	mΩ
		V _{GS} = 4.5 V, I _S = 5 A	7.9	9.9	11.9	mΩ
g _{fs}	Transconductance	V _{S1S2} = 1.2 V, I _S = 5 A	36			S
DYNAMIC CHARACTERISTICS ⁽¹⁾						
C _{iss}	Input capacitance	V _{GS} = 0 V, V _{S1S2} = 6 V, f = 1 MHz		902	1170	pF
C _{oss}	Output capacitance			187	243	pF
C _{rss}	Reverse transfer capacitance			111	144	pF
Q _g	Gate charge total (4.5 V)	V _{S1S2} = 6 V, I _S = 5 A		8.4	10.9	nC
Q _{gd}	Gate charge gate-to-drain			1.9		nC
Q _{gs}	Gate charge gate-to-source			2.2		nC
Q _{g(th)}	Gate charge at V _{th}			0.6		nC
Q _{oss}	Output charge	V _{S1S2} = 6 V, V _{GS} = 0 V		2.9		nC
t _{d(on)}	Turnon delay time	V _{S1S2} = 6 V, V _{GS} = 4.5 V, I _{S1S2} = 5 A, R _G = 0 Ω		205		ns
t _r	Rise time			353		ns
t _{d(off)}	Turnoff delay time			711		ns
t _f	Fall time			589		ns
DIODE CHARACTERISTICS						
V _{F(S-S)}	Source-to-source diode forward voltage	I _{SS} = 5 A, V _{G1S1} = 0 V, V _{G2S2} = 4.5 V		0.79	1.0	V

(1) Dynamic characteristics values specified are per single FET.

4.2 Thermal Information

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾		150		$^\circ\text{C/W}$
	Junction-to-ambient thermal resistance ⁽²⁾		55		

(1) Device mounted on FR4 material with minimum Cu mounting area.

(2) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.

4.3 Typical MOSFET Characteristics

$T_A = 25^\circ\text{C}$ (unless otherwise stated)

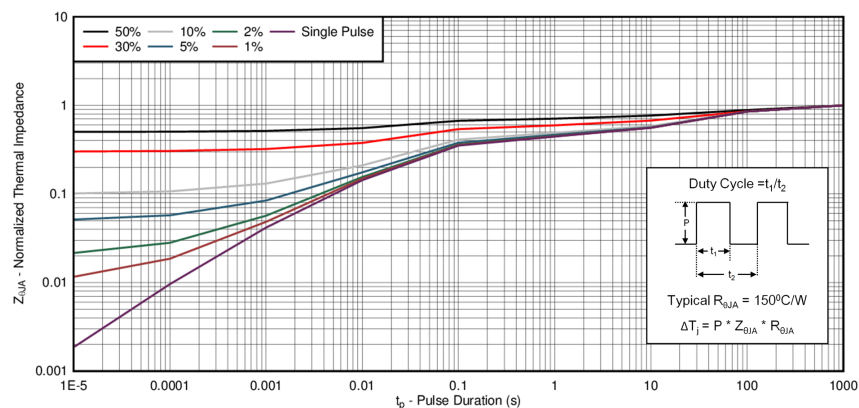


图 4-1. Transient Thermal Impedance

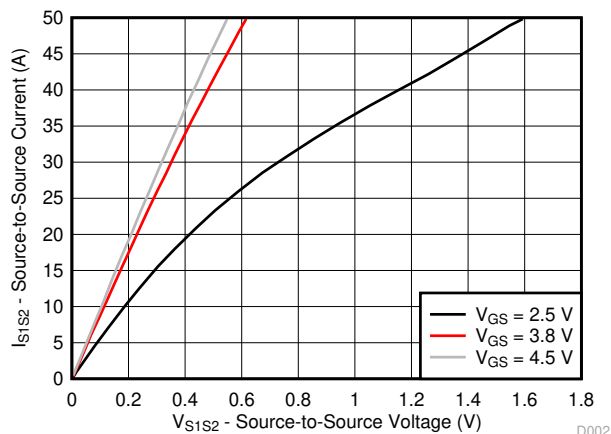


图 4-2. Saturation Characteristics

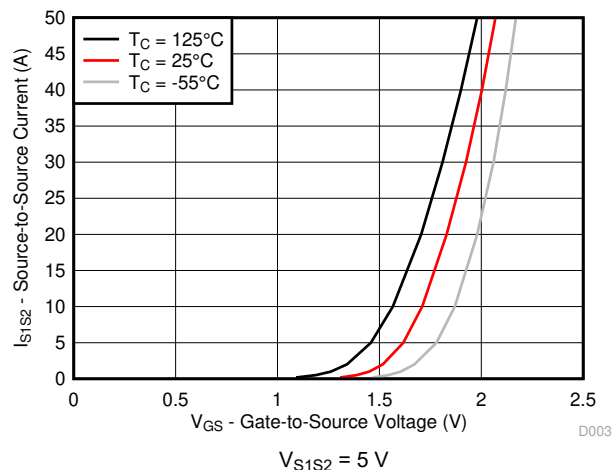


图 4-3. Transfer Characteristics

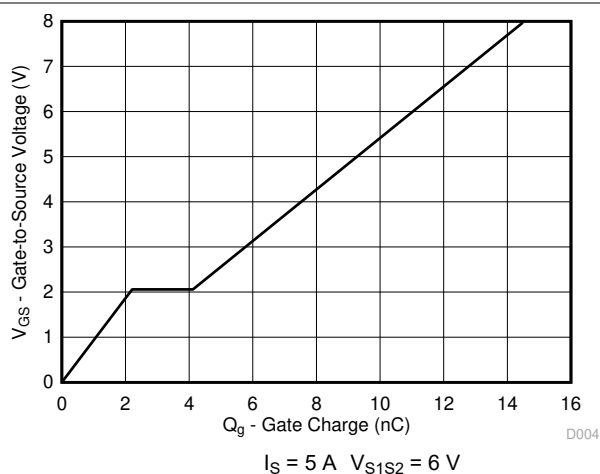


图 4-4. Gate Charge

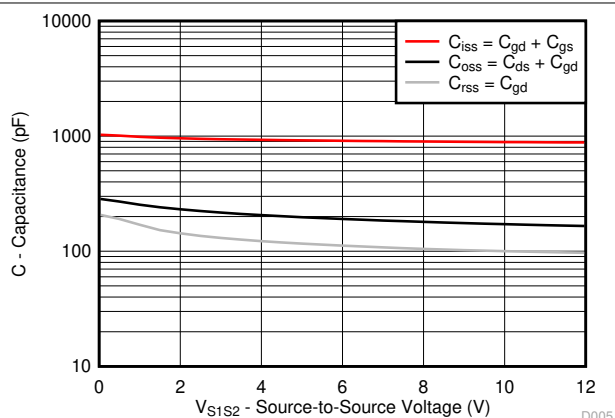


图 4-5. Capacitance

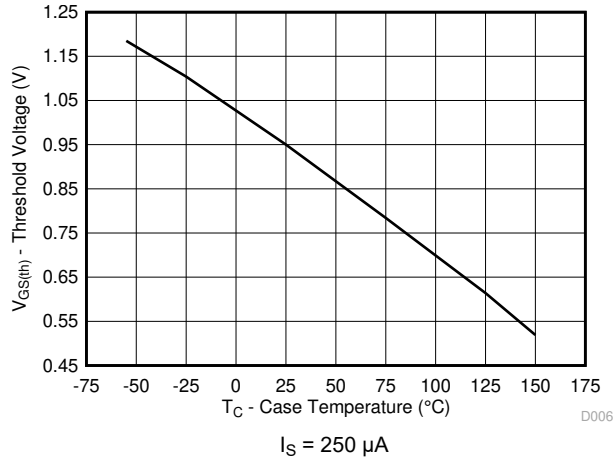


图 4-6. Threshold Voltage vs Temperature

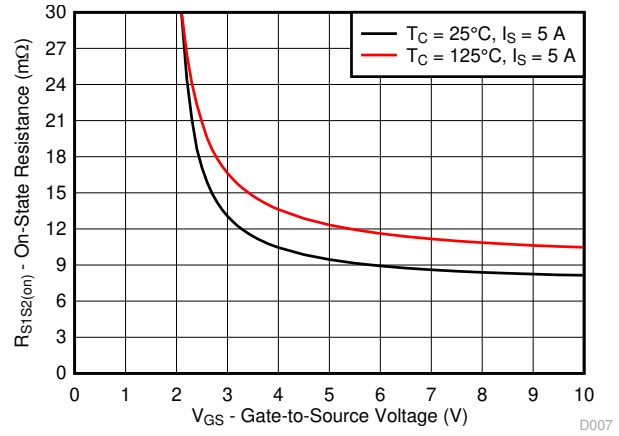


图 4-7. On-State Source-to-Source Resistance vs Gate-to-Source Voltage

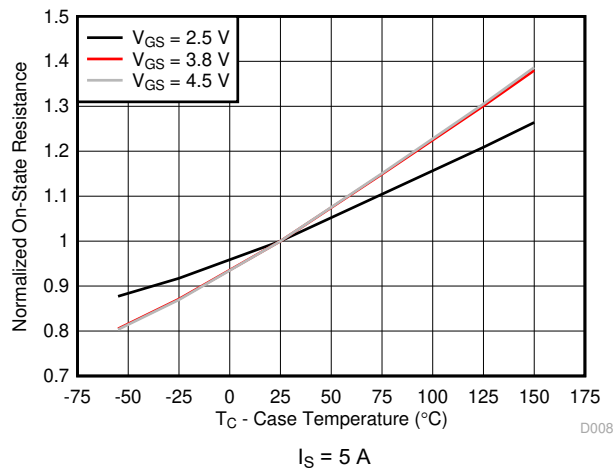


图 4-8. Normalized On-State Resistance vs Temperature

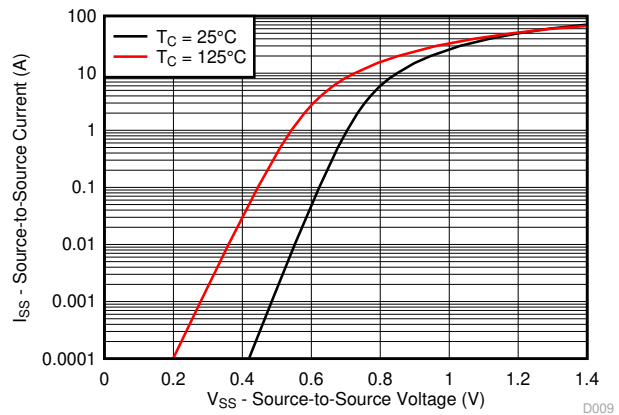


图 4-9. Typical Diode Forward Voltage

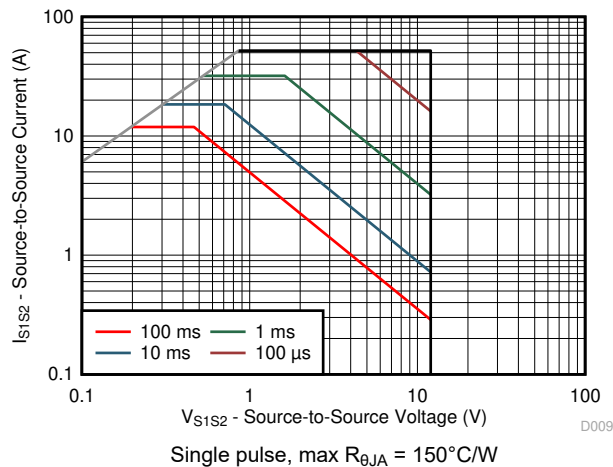


图 4-10. Maximum Safe Operating Area

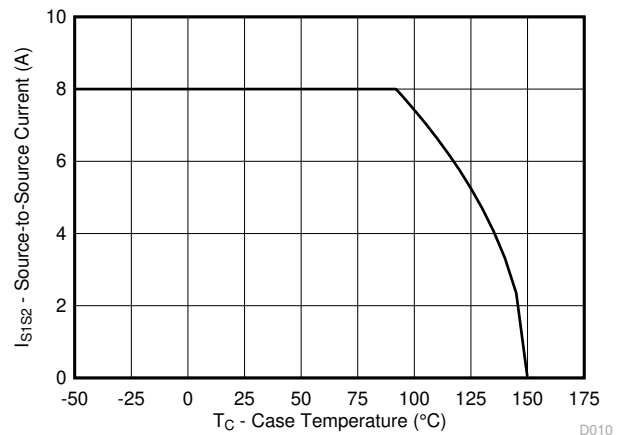


图 4-11. Maximum Source Current vs Temperature

5 Device and Documentation Support

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5.3 支持资源

TI E2E™ [中文支持论坛](#) 是工程师的重要参考资料，可直接从专家处获得快速、经过验证的解答和设计帮助。搜索现有解答或提出自己的问题，获得所需的快速设计帮助。

链接的内容由各个贡献者“按原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的 [使用条款](#)。

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

5.6 术语表

TI 术语表

本术语表列出并解释了术语、首字母缩略词和定义。

6 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision B (February 2017) to Revision C (November 2023)	Page
• 将阈值电压 $GS(th)$ 从 0.95V 更新为 1.0V.....	1
• 更新了整个文档中的表格、图和交叉参考的编号格式.....	1
• Updated Source-to-source on resistance $V_{GS} = 2.5\text{ V}$ from 14 mΩ to 12 mΩ.....	3
• Updated Gate-to-source threshold voltage from 0.75 V min, 0.95 V typ, 1.25 V max to 0.7 V min, 1.0 V typ, 1.4 V max.....	3
Changes from Revision A (January 2016) to Revision B (February 2017)	Page
• Added Diode Characteristics ($V_{F(S-S)}$) in the <i>Electrical Characteristics</i> table.....	3
• Added 图 4-9 to <i>Typical MOSFET Characteristics</i> section.....	4
Changes from Revision * (November 2014) to Revision A (January 2016)	Page
• Improved graph setup for readability.....	4

7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CSD83325L	Active	Production	PICOSTAR (YJE) 6	3000 LARGE T&R	Yes	NIAU	Level-1-260C-UNLIM	-	83325L
CSD83325L.B	Active	Production	PICOSTAR (YJE) 6	3000 LARGE T&R	Yes	NIAU	Level-1-260C-UNLIM	-55 to 150	83325L
CSD83325LT	Active	Production	PICOSTAR (YJE) 6	250 SMALL T&R	Yes	NIAU	Level-1-260C-UNLIM	-55 to 150	83325L
CSD83325LT.B	Active	Production	PICOSTAR (YJE) 6	250 SMALL T&R	Yes	NIAU	Level-1-260C-UNLIM	-55 to 150	83325L

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "-" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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TAPE AND REEL INFORMATION



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD83325L	PICOSTAR	YJE	6	3000	180.0	8.4	1.25	2.34	0.32	4.0	8.0	Q1
CSD83325LT	PICOSTAR	YJE	6	250	180.0	8.4	1.25	2.34	0.32	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD83325L	PICOSTAR	YJE	6	3000	182.0	182.0	20.0
CSD83325LT	PICOSTAR	YJE	6	250	182.0	182.0	20.0

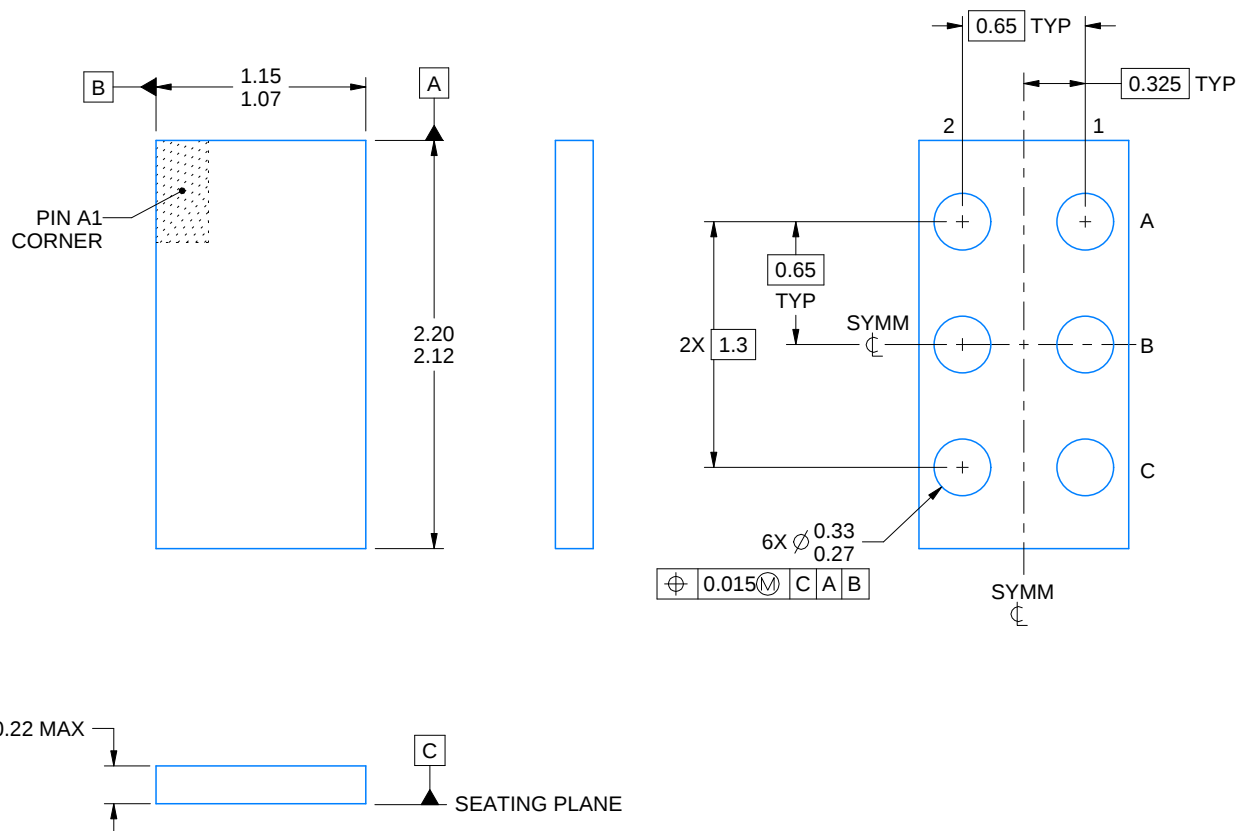
YJE0006A



PACKAGE OUTLINE

PicoStar™ - 0.22 mm max height

PicoStar



D: Max = 2.19 mm, Min = 2.13 mm

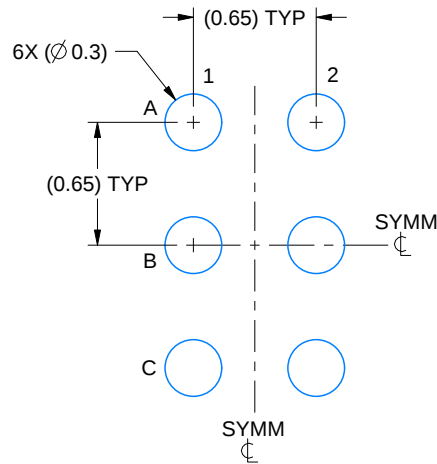
E: Max = 1.14 mm, Min = 1.08 mm

4221674/C 07/2023

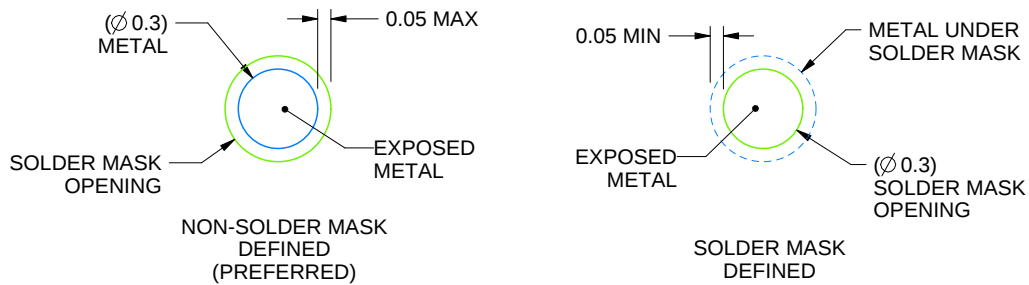
NOTES:

PicoStar is a trademark of Texas Instruments.

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:25X

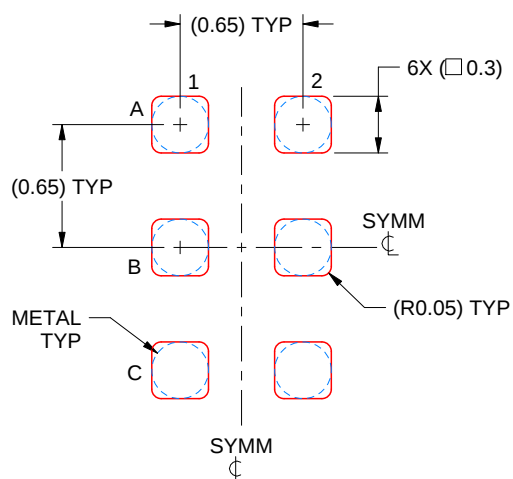


SOLDER MASK DETAILS
NOT TO SCALE

4221674/C 07/2023

NOTES: (continued)

- Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).



SOLDER PASTE EXAMPLE
 BASED ON 0.1 mm THICK STENCIL
 SCALE:25X

4221674/C 07/2023

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.

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